APR 1 5 2004 21

In place of	
PTO-1449	
Carm	

SHEET

U. S. DEPARTMENT OF COMMERCE

OF

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known					
Application Number	10/712,460				
Filing Date	November 13, 2003				
Applicant(s)	Chia-Lin Chen, et al.				
Art Unit	4746 2826				
Examiner Name	To Be Determined a Everhant				
Attorney Docket Number	24061.42 (TSMC2002-1015)				

			U. S. PATENT D	OCUMENTS
Examiner's	Cite No.	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document Tay et al.
BIME.	AA	2002/0009900	01/24/02	Tay et al.
1	AB	5,371,396	12/06/94	Vinal et al.
	AC	5,521,127	05/28/96	Hori et al.
	AD	5,710,450	01/20/98	Chau et al.
	AE	5,840,125	11/24/98	Gronet et al.
7	AF	5,943,230	08/24/99	Rinnen et al.
	AG	5,959,333	09/28/99	Gardner et al.
	AH	6,020,260	02/01/00	Gardner
	Al	6,099,647	08/08/00	Yich et al.
	AJ	6,110,812	08/28/00	Ho et al.
	AK	6,114,258	09/05/00	Miner et al.
	AL	6,159,866	12/12/00	Gronet et al.
	AM	6,207,304	03/27/01	Law et al.
	AN	6,242,776	06/05/01	Hause et al.
	AO	6,323,094	11/27/01	Wu
	AP	6,326,664	12/04/01	Chau et al.
	AQ	6,399,445	06/04/02	Hattangady, et al.
	AR	6,402,850	06/11/02	Beinglass et al.
	AS	6,410,090	06/25/02	Wang
	AT	6,413,871	07/02/02	M'Saad et al.
	AU	6,450,116	09/17/02	Noble et al.
	AV	6,482,726	11/19/02	Aminpur et al.
	AW	6,488,776	12/03/02	Wang
DEME.	AX	6,518,203	02/11/03	Narwankar et al.

FOREIGN PATENT DOCUMENTS					
Examiners Cite No.	Foreign Paten Document Country Code - Number	Publication MH-00 Y	Date Patento	e or Applicant of Cite Document	di Translation

		OTHER PRIOR ART
*Examiners	Cite No.	Pinclude name of the author (in CAPITAL LETTERS), title of the article title of the item, date; page(s), volume
CYME.	AY	ARNUAD, F., ET AL., "Gate Oxide Process Impact on RNCE for Advanced CMOS Transistors", September 2002, ESSDERC '02, Firenze Italy, 21 pages.
CUME	AZ	LI, GENE, "Total Solutions for Front-End Thermal Processing", Foresight, May 2001, Pages 41-45.
CYME	BA	ZONCA, R., ET AL., "Ultra Thin NO/N₂O Oxynitride Dielectric for Advanced Flash Memory Application: Single Wafer and Batch Technology", 6 pages.
dype	BB	"Gate Stack", World Wide Web http://www.appliedmaterials.com/products/gate_stack.html, printed on February 17, 2003, 1 page.
1 cme	BC	"Technology Challenges for 100nn and Beyond Transistor and Capacitor Fabrication: Fig. 8", World Wide Web http://www.future-fab.com/assets/images/FFI11E1104F8.htm, printed on February 18, 2003, 1 page.

Examiner Signature	& kuerhark	Date	15/20
Signature	- Court	Considered	7.5/09

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.

								·	-i
In place of PTO-1449	In place of U. S. DEPARTMENT OF COMMERCE PTO-1449 PATENT AND TRADEMARK OFFICE Form			Complete if Known					
11						Applicati	on Number	10/712,460	
E INFO	INFORMATION DISCLOSURE					Filing Date		11/13/2003	
STA	STATEMENT BY APPLICANT					Applicant(s)		Chen et al.	
	(use as many sheets as necessary)					Art Unit	``	9748 2426	
12 T	C:				Examiner Name		To Be Determined	C. Everhar	
SHEET		1	OF	1			Docket Number	TSMC2002-1015/2	C, C, C
AT & TRAPE		—			!	,			
WY TO			·	_l	J. S. PA	TENT DO	CUMENTS		
Examiner's Initials	Cite No.	Docu	ment Nun			on Date		Patentee or Applican	t of Cited Document
OME	AA	645540			09/2	002	Linderer et al.	-	
ame	AB	653440	1		03/2	003	Joo et al.		
•		ļ							
		 							
		 							
 		 	, , , , , , , , , , , , , , , , , , , ,					··	
	_	 							
							·		
		ļ							
		 						· · · · · · · · · · · · · · · · · · ·	· - · · · · · · · · · · · · · · · · · · ·
	·-·	 							
		 							
		 							
		ļ							
		<u> </u>							
		 							
L		L	···			-			
				FOI	REIGN	PATENT	OCUMENTS		
Examiner's	Cite	For	eign Pater	nt F	ublicati	on Date	Patentee or A	pplicant of Cited	Translation

	FOREIGN PATENT DOCUMENTS								
Examiner's Initials	Cite No.	Foreign Patent Document (Country Code - Number - Kind)	Publication Date	Patentee or Applicant of Cited Document	Translation				

NON-PATENT LITERATURE					
Examiner's	Cite	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume			
Initials	No.	issue number(s), publisher, city/country where published			
ome	AC	Decoupled Plasma Nitridation (DPN), May 2001, Foresight, Pages 43-45.			

Examiner	1 0	1 1-	 Date	
	16 11	erkast	Date	10-15-04
Signature	· /w	e cos.	Considered	10-04
			 1 30110100100	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.